



# GMA01, 01U

Epitaxial Planar Silicon Diode  
**Very High-Speed Switching,  
 Bias Stabilizing Applications**

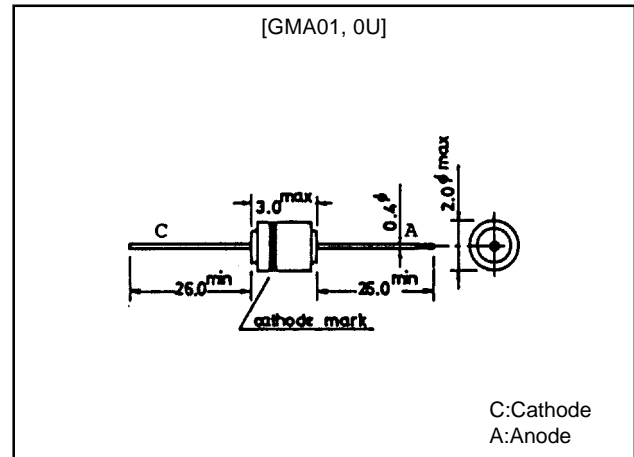
## Features

- Glass sleeve structure.
- Allowable power dissipation :  $P=300\text{mW}$  max.
- Interterminal capacitance :  $c=3.0\text{pF}$  max.
- Reverse recovery time :  $t_{rr}=4.0\text{ns}$  max.
- Small size, being about half of DO-35 package heretofore in use.

## Package Dimensions

unit:mm

1114



## Specifications

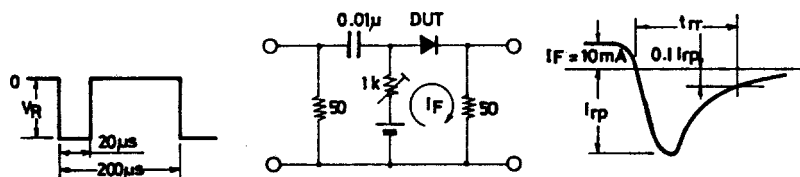
### Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	GMA01	GMA01U	Unit
Peak Reverse Voltage	$V_{RM}$		60	105	V
Reverse Voltage	$V_R$		55	100	V
Peak Forward Current	$I_{FM}$		→	360	mA
Average Rectified Current	$I_O$		→	120	mA
Surge Forward Current	$I_{FSM}$	1 s pulse	→	500	mA
Allowable Power Dissipation	P		→	300	mW
Junction Temperature	$T_j$		→	175	$^\circ\text{C}$
Storage Temperature	$T_{stg}$		→	-65 to +175	$^\circ\text{C}$

### Electrical Characteristics at $T_a = 25^\circ\text{C}$

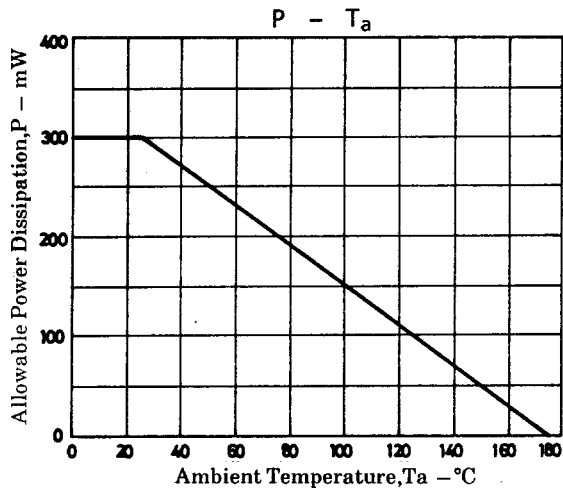
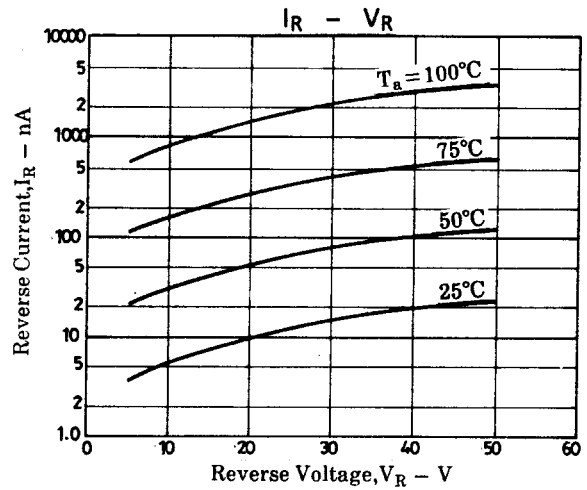
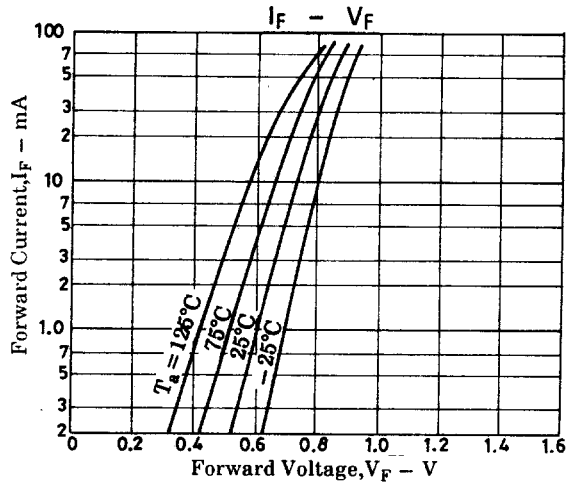
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Forward Voltage	$V_F$	$I_F=1.5\text{mA}$	0.55		0.68	V
Reverse Current	$I_R$	$V_R=55$ (GMA01)			0.5	$\mu\text{A}$
		$V_R=75$ (GMA01U)			0.5	$\mu\text{A}$
		$V_R=100\text{V}$ (GMA01U)			5	$\mu\text{A}$
Interterminal Capacitance	C	$V_R=0, f=1\text{MHz}$			3.0	pF
Reverse Recovery Time	$t_{rr}$	$V_R=6\text{V}, I_F=10\text{mA}, R_L=50\Omega$			4.0	ns

### Reverse Recovery Time Test Circuit

Unit (resistance :  $\Omega$ , capacitance : F)

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